



A625308A Series

32K X 8 BIT CMOS SRAM

Document Title

32K X 8 BIT CMOS SRAM

Revision History

<u>Rev. No.</u>	<u>History</u>	<u>Issue Date</u>	<u>Remark</u>
0.0	Initial issue	February 2, 2001	Preliminary
0.1	Add ultra temp grade and 28-pin DIP package type	November 7, 2001	
0.2	Add SI grade	July 17, 2002	
1.0	Final version release	July 16, 2003	Final
1.1	Add Pb-Free package type	August 19, 2004	
1.2	Remove non-Pb-free package type	July 3, 2006	
1.3	Remove DIP -SI and -SU grade	September 26, 2006	



A625308A Series

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Features

- Power Supply Range: 4.5V to 5.5V
- Access times: 70 ns
 - A625308A-S series: Operating: 35mA (max.)
Standby: 10µA (max.)
 - A625308A-SI/SU series: Operating: 35mA (max.)
Standby: 15µA (max.)
- Extended operating temperature range: 0°C to 70°C for -S series, -25°C to 85°C for -SI series, -40°C to 85°C for -SU series.
- Full static operation, no clock or refreshing required
- All inputs and outputs are directly TTL-compatible
- Common I/O using three-state output
- Data retention voltage: 2.0V (min.)
- Available in 28-pin, DIP/SOP and TSOP
- Pb-Free package only
- All Pb-free (Lead-free) products are RoHS compliant

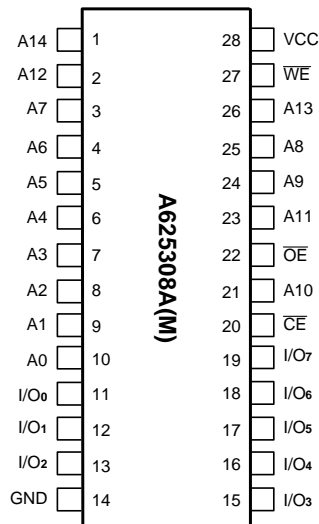
General Description

The A625308A is a low operating current 262,144-bit static random access memory organized as 32,768 words by 8 bits and operates on a voltage from 4.5V to 5.5V. Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

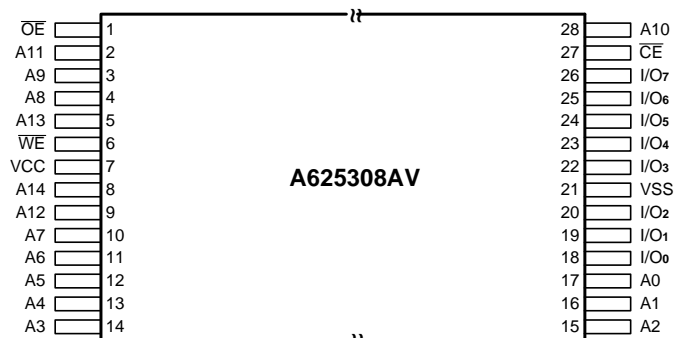
Minimum standby power is drawn by this device when \overline{CE} is at a high level, independent of the other input levels. Data retention is guaranteed at a power supply voltage as low as 2.0V.

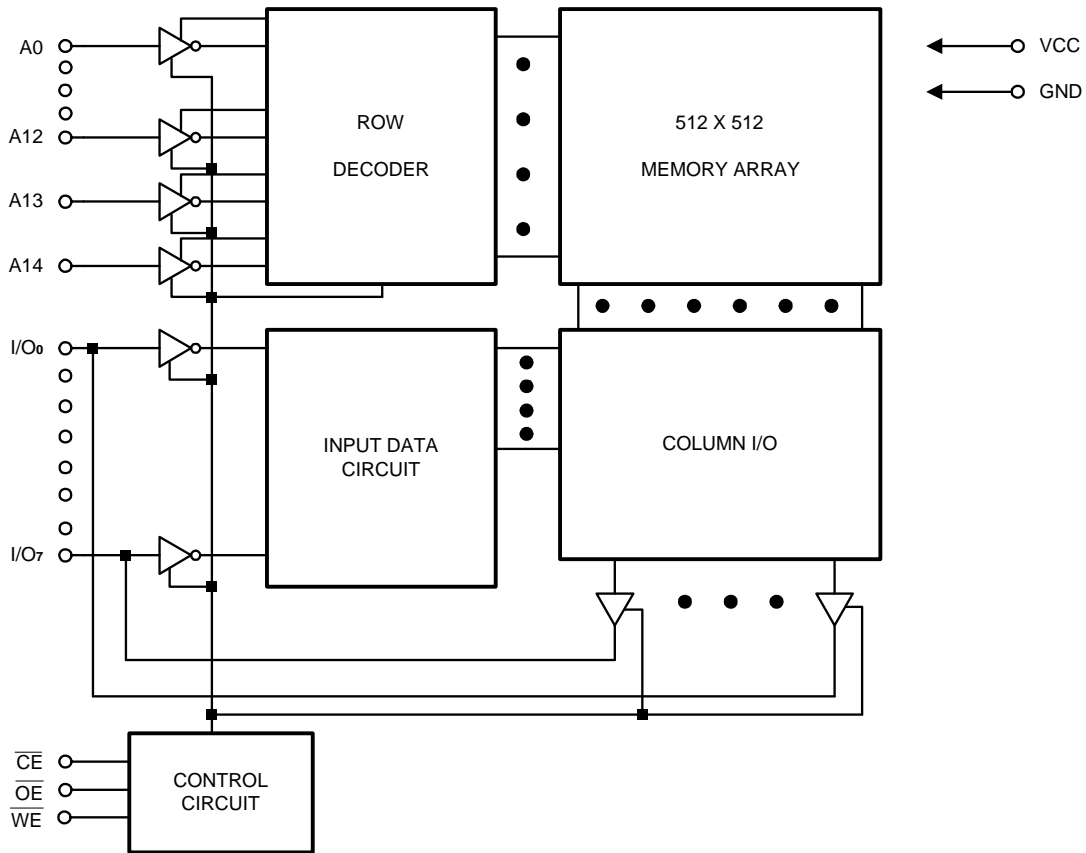
Pin Configurations

■ DIP / SOP



■ TSOP



Block Diagram

Pin Descriptions – DIP / SOP

Pin No.	Symbol	Description
1-10, 21, 23-26	A0 - A14	Address Input
11-13, 15-19	I/O ₀ - I/O ₇	Data Input/Output
20	\overline{CE}	Chip Enable
22	\overline{OE}	Output Enable
27	\overline{WE}	Write Enable
28	VCC	Power Supply
14	GND	Ground

Pin Description-TSOP

Pin No.	Symbol	Description
2-5, 8-17, 28	A0 - A14	Address Input
18-20, 22-26	I/O ₀ - I/O ₇	Data Input/Output
27	\overline{CE}	Chip Enable
1	\overline{OE}	Output Enable
6	\overline{WE}	Write Enable
7	VCC	Power Supply
21	GND	Ground

Recommended DC Operating Conditions

 (T_A = 0°C to +70°C, -25°C to +85°C or -40°C to +85°C)

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V _{IH}	Input High Voltage	2.2	-	VCC + 0.5	V
V _{IL}	Input Low Voltage	-0.5	0	+0.8	V

Absolute Maximum Ratings*

VCC to GND -0.5V to +7.0V
 IN, IN/OUT Volt to GND -0.5V to VCC + 0.5V
 Operating Temperature, Topr
 0°C to +70°C or -40°C to +85°C
 Storage Temperature, Tstg -55°C to +125°C
 Power Dissipation, PT 0.7W
 Soldering Temp. & Time 260°C, 10 sec

***Comments**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied and exposure to absolute maximum rating conditions for extended periods may affect device reliability.

DC Electrical Characteristics (T_A = 0°C to +70°C, -25°C to +85°C or -40°C to +85°C, VCC = 5.0V ± 10%, GND = 0V)

Symbol	Parameter	A625308A-70S		A625308A-70SI/SU		Unit	Conditions
		Min.	Max.	Min.	Max.		
I _{LI}	Input Leakage Current	-	1	-	1	μA	V _{IN} = GND to VCC
I _{LO}	Output Leakage Current	-	1	-	1	μA	\overline{CE} = V _{IH} V _{I/O} = GND to VCC
I _{CC}	Active Power Supply Current	-	5	-	5	mA	\overline{CE} = V _{IL} , I _{I/O} = 0mA
I _{CC1}	Dynamic Operating Current	-	35	-	35	mA	Min. Cycle, Duty = 100% \overline{CE} = V _{IL} , I _{I/O} = 0mA
I _{CC2}	Dynamic Operating Current	-	5	-	5	mA	\overline{CE} = V _{IL} , V _{IH} = VCC V _{IL} = 0V, f = 1 MHz I _{I/O} = 0 mA
I _{SB}	Supply Current Standby Power	-	0.5	-	0.5	mA	\overline{CE} = V _{IH}
I _{SB1}		-	10	-	15	μA	\overline{CE} ≥ VCC - 0.2V V _{IN} ≥ 0V
V _{OL}	Output Low Voltage	-	0.4	-	0.4	V	I _{OL} = 2.1 mA
V _{OH}	Output High Voltage	2.4	-	2.4	-	V	I _{OH} = -1.0 mA

Truth Table

Mode	$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	I/O Operation	Supply Current
Standby	H	X	X	High Z	$I_{\text{SB}}, I_{\text{SB1}}$
Output Disable	L	H	H	High Z	$I_{\text{CC}}, I_{\text{CC1}}, I_{\text{CC2}}$
Read	L	L	H	DOUT	$I_{\text{CC}}, I_{\text{CC1}}, I_{\text{CC2}}$
Write	L	X	L	DIN	$I_{\text{CC}}, I_{\text{CC1}}, I_{\text{CC2}}$

Note: X: H or L

Capacitance ($T_A = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$)

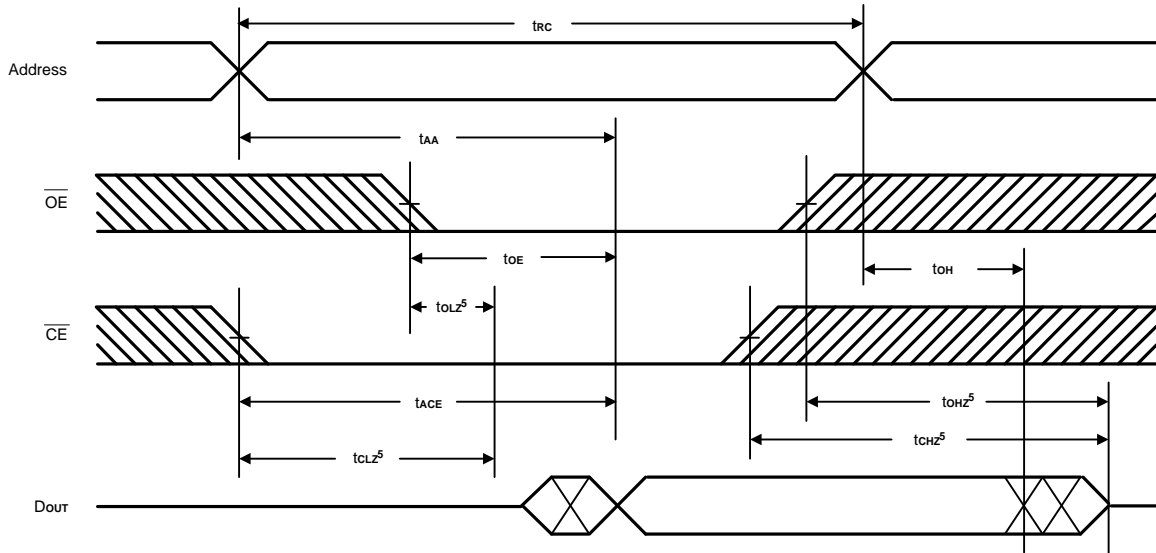
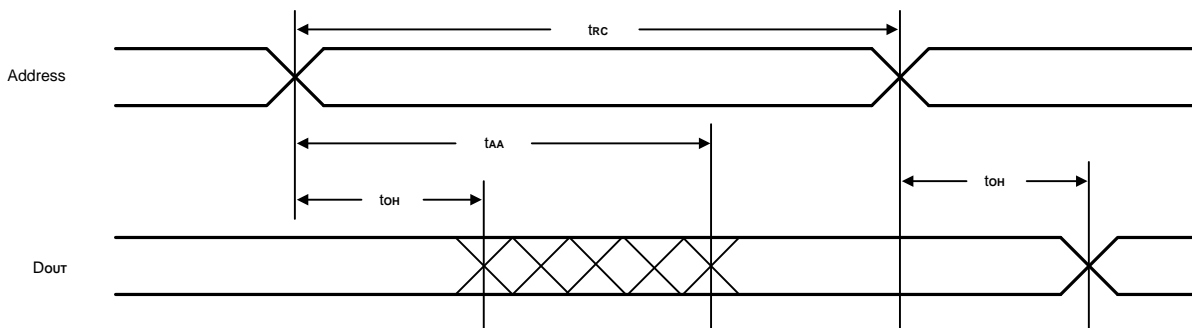
Symbol	Parameter	Min.	Max.	Unit	Conditions
C_{IN}^*	Input Capacitance	-	6	pF	$V_{\text{IN}} = 0\text{V}$
C_{IO}^*	Input/Output Capacitance	-	8	pF	$V_{\text{IO}} = 0\text{V}$

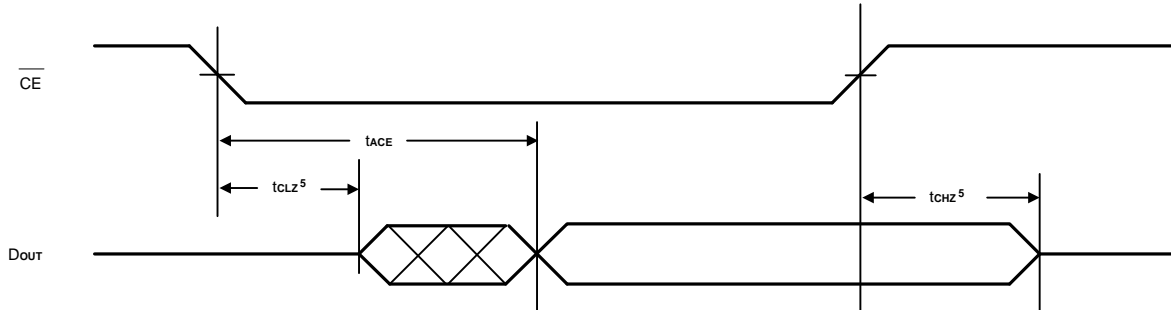
* These parameters are sampled and not 100% tested.

AC Characteristics ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, -25°C to $+85^\circ\text{C}$ or -40°C to $+85^\circ\text{C}$, $V_{CC} = 5.0\text{V} \pm 10\%$)

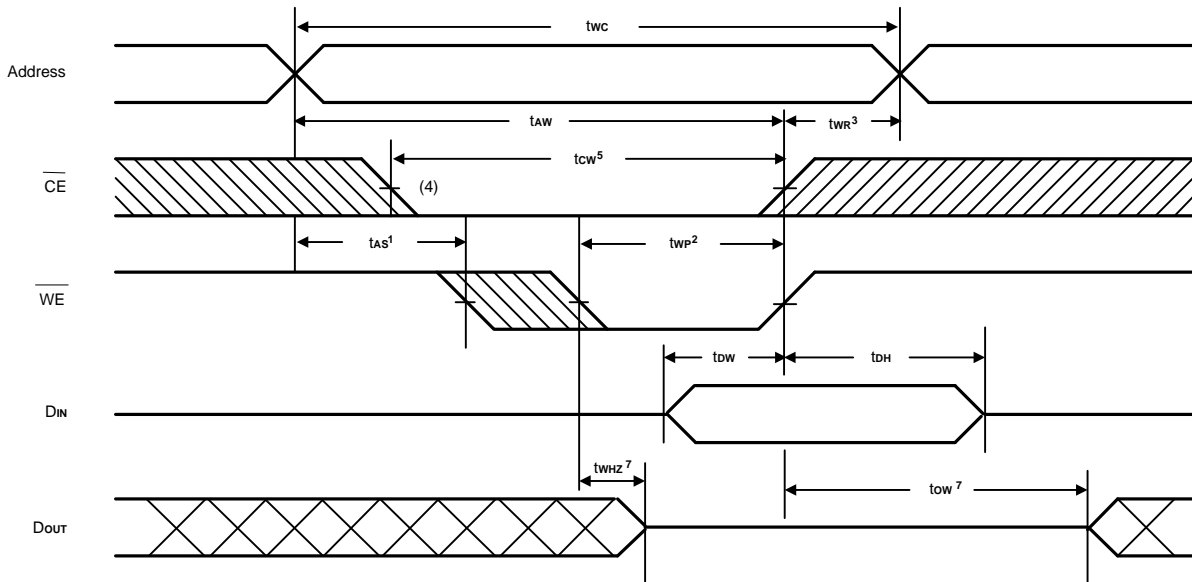
Symbol	Parameter	A625308A-70S/SI/SU		Unit
		Min.	Max.	
Read Cycle				
trc	Read Cycle Time	70	-	ns
tAA	Address Access Time	-	70	ns
tACE	Chip Enable Access Time	-	70	ns
toE	Output Enable to Output Valid	-	35	ns
tCLZ	Chip Enable to Output in Low Z	10	-	ns
toLZ	Output Enable to Output in Low Z	5	-	ns
tCHZ	Chip Disable to Output in High Z	-	25	ns
toHZ	Output Disable to Output in High Z	-	25	ns
toH	Output Hold from Address Change	10	-	ns
Write Cycle				
twc	Write Cycle Time	70	-	ns
tcw	Chip Enable to End of Write	60	-	ns
tAS	Address Set up Time	0	-	ns
tAW	Address Valid to End of Write	60	-	ns
tWP	Write Pulse Width	50	-	ns
tWR	Write Recovery Time	0	-	ns
tWHZ	Write to Output in High Z	-	25	ns
tdw	Data to Write Time Overlap	30	-	ns
tdH	Data Hold from Write Time	0	-	ns
tow	Output Active from End of Write	5	-	ns

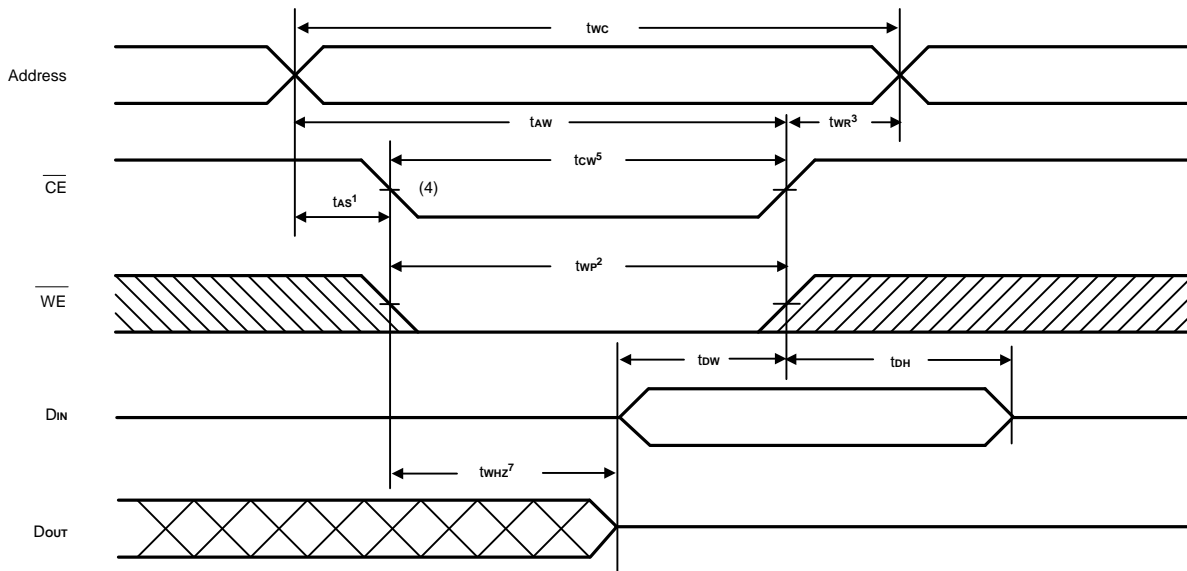
Notes: tCHZ, toHZ and tWHZ are defined as the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.

Timing Waveforms
Read Cycle 1 ⁽¹⁾

Read Cycle 2 ^(1, 2, 4)


Timing Waveforms (continued)
Read Cycle 3 (1, 3, 4)


- Notes:
1. \overline{WE} is high for Read Cycle.
 2. Device is continuously enabled, $\overline{CE} = V_{IL}$.
 3. Address valid prior to or coincident with \overline{CE} transition low.
 4. $\overline{OE} = V_{IL}$.
 5. Transition is measured $\pm 500\text{mV}$ from steady state. This parameter is sampled and not 100% tested.

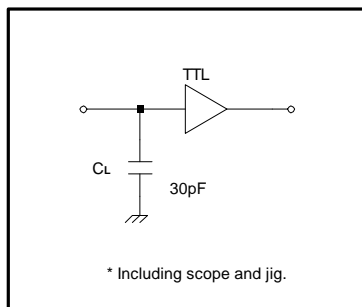
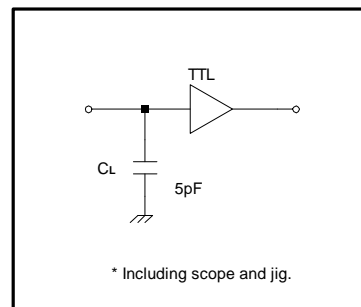
**Write Cycle 1 (6)
(Write Enable Controlled)**


Timing Waveforms (continued)
**Write Cycle 2 ⁽⁶⁾
(Chip Enable Controlled)**


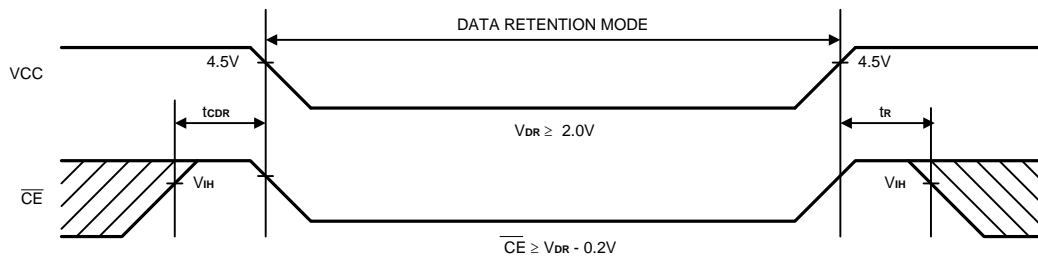
- Notes:
1. t_{as} is measured from the address valid to the beginning of Write.
 2. A Write occurs during the overlap (t_{wp}) of a low \overline{CE} and a low \overline{WE} .
 3. t_{wr} is measured from the earliest of \overline{CE} or \overline{WE} going high to the end of the Write cycle.
 4. If the \overline{CE} low transition occurs simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, outputs remain in a high impedance state.
 5. t_{cw} is measured from the later of \overline{CE} going low to the end of Write.
 6. \overline{OE} level is high or low.
 7. Transition is measured $\pm 500\text{mV}$ from steady. This parameter is sampled and not 100% tested.

AC Test Conditions

Input Pulse Levels	0V, 3V
Input Rise And Fall Time	5 ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Figure 1 and 2


Figure 1. Output Load

Figure 2. Output Load for t_{CLZ1} , t_{CLZ2} , t_{OHZ} , t_{OLZ} , t_{CHZ1} , t_{CHZ2} , t_{WHZ} , and t_{OW}
Data Retention Characteristics ($T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$, -25°C to $+85^\circ\text{C}$ or -40°C to $+85^\circ\text{C}$)

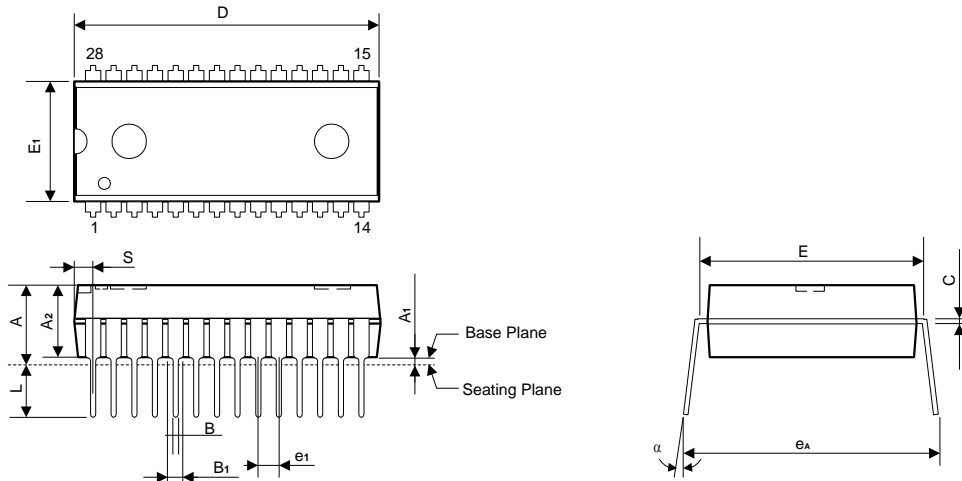
Symbol	Parameter	Min.	Max.	Unit	Conditions
V_{DR}	VCC for Data Retention	2.0	5.5	V	$\overline{CE} \geq VCC - 0.2V$
I_{CCDR}	Data Retention Current	-	3	μA	$VCC = 2.0V$, $\overline{CE} \geq VCC - 0.2V$ $V_{IN} \geq 0V$
t_{CDR}	Chip Disable to Data Retention Time	0	-	ns	See Retention Waveform
t_R	Operation Recovery Time	t_{RC}	-	ns	

Low VCC Data Retention Waveform

Ordering Information

Part No.	Access Time (ns)	Operating Current Max. (mA)	Standby Current Max. (μA)	Package
A625308A-70SF	70	35	10	28L Pb-Free DIP
A625308AM-70SF		35	10	28L Pb-Free SOP
A625308AV-70SF		35	10	28L Pb-Free TSOP (Forward)
A625308AM-70SIF		35	15	28L Pb-Free SOP
A625308AV-70SIF		35	15	28L Pb-Free TSOP (Forward)
A625308AM-70SUF		35	15	28L Pb-Free SOP
A625308AV-70SUF		35	15	28L Pb-Free TSOP (Forward)

Package Information
P-DIP 28L Outline Dimensions

unit: inches/mm



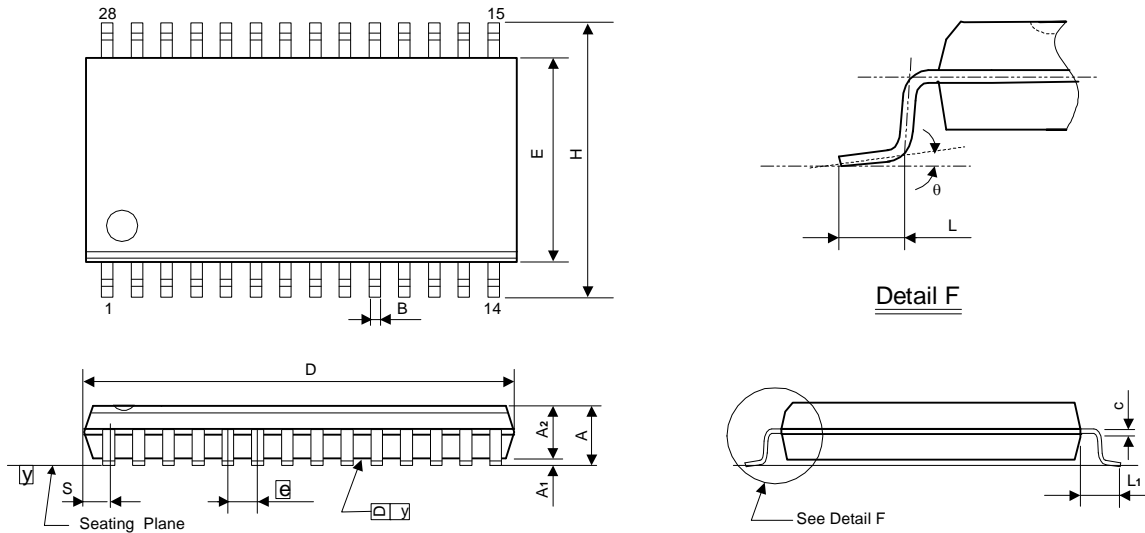
Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.210	-	-	5.33
A1	0.010	-	-	0.25	-	-
A2	0.150	0.155	0.160	3.81	3.94	4.06
B	0.016	0.018	0.022	0.41	0.46	0.56
B1	0.058	0.060	0.064	1.47	1.52	1.63
C	0.008	0.010	0.014	0.20	0.25	0.36
D	-	1.460	1.470	-	37.08	37.34
E	0.590	0.600	0.610	14.99	15.24	15.49
E1	0.540	0.545	0.550	13.72	13.84	13.97
e1	0.090	0.100	0.110	2.29	2.54	2.79
L	0.120	0.130	0.140	3.05	3.30	3.56
alpha	0°	-	15°	0°	-	15°
eA	0.630	0.650	0.670	16.00	16.51	17.02
S	-	-	0.090	-	-	2.29

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E1 does not include resin fins.
3. Dimension S includes end flash.

Package Information
SOP (W.B.) 28L Outline Dimensions

unit: inches/mm



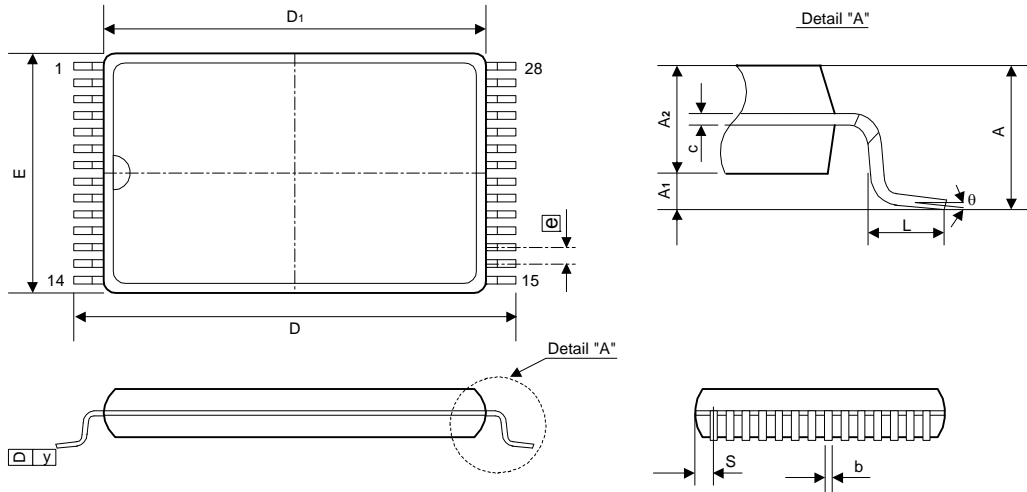
Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.112	-	-	2.85
A1	0.004	-	-	0.10	-	-
A2	0.093	0.098	0.103	2.36	2.49	2.62
B	0.014	0.016	0.020	0.36	0.41	0.51
C	0.008	0.010	0.012	0.20	0.25	0.30
D	-	0.713	0.728	-	18.11	18.49
E	0.326	0.331	0.336	8.28	8.41	8.53
e	0.044	0.050	0.056	1.12	1.27	1.42
H	0.453	0.465	0.477	11.51	11.81	12.12
L	0.028	0.036	0.044	0.71	0.91	1.12
L1	0.059	0.067	0.075	1.50	1.70	1.91
S	-	-	0.047	-	-	1.19
y	-	-	0.004	-	-	0.10
θ	0°	-	8°	0°	-	8°

Notes:

1. The maximum value of dimension D includes end flash.
2. Dimension E does not include resin fins.
3. Dimension S includes end flash.

Package Information
TSOP 28L TYPE I (8 X 13.4mm) Outline Dimensions

unit: inches/mm



Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.049	-	-	1.25
A ₁	0.002	-	-	0.05	-	-
A ₂	0.037	0.039	0.041	0.95	1.00	1.05
b	0.007	0.009	0.011	0.17	0.22	0.27
c	0.005	-	0.008	0.12	-	0.21
E	0.311	0.315	0.319	7.90	8.00	8.10
L	0.012	0.020	0.028	0.30	0.50	0.70
D	0.520	0.528	0.536	13.20	13.40	13.60
D ₁	0.461	0.465	0.469	11.70	11.80	11.90
e	0.022 BSC			0.55 BSC		
S	0.017 TYP			0.425 TYP		
y	-	-	0.004	-	-	0.10
θ	0°	-	5°	0°	-	5°

Notes:

1. The maximum value of dimension D₁ includes end flash.
2. Dimension E does not include resin fins.
3. Dimension S includes end flash.